

SANYO

No.3466

2SK1463

N-Channel MOS Silicon FET

Very High-Speed Switching Applications

Features

- Low ON-state resistance.
- Very high-speed switching.
- Converters.

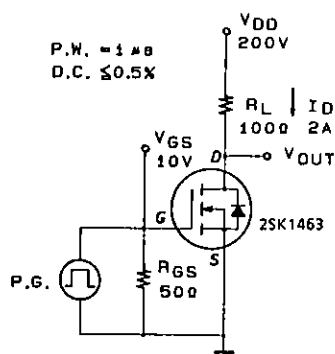
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Drain to Source Voltage	V_{DS}	900	V
Gate to Source Voltage	V_{GS}	± 30	V
Drain Current(DC)	I_D	4.5	A
Drain Current(Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	A
Allowable Power Dissipation	P_D	$T_c = 25^\circ\text{C}$	60 W
			3.0 W
Channel Temperature	T_{ch}		150°C
Storage Temperature	T_{stg}		$-55 \text{ to } +150^\circ\text{C}$

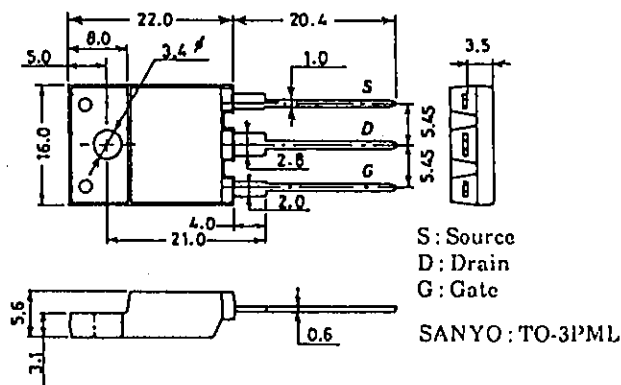
Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}, V_{GS} = 0$	900			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 900\text{V}, V_{GS} = 0$			1.0	mA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{V}, V_{DS} = 0$			± 100	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	2.0		3.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 20\text{V}, I_D = 2\text{A}$	1.0	2.0		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = 2\text{A}, V_{GS} = 10\text{V}$		2.8	3.6	Ω
Input Capacitance	C_{iss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		700		pF
Output Capacitance	C_{oss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		300		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 20\text{V}, f = 1\text{MHz}$		170		pF
Turn-ON Delay Time	$t_{d(on)}$	$I_D = 2\text{A}, V_{GS} = 10\text{V}$ $V_{DD} = 200\text{V}, R_{GS} = 50\Omega$		15		ns
Rise Time	t_r			35		ns
Turn-OFF Delay Time	$t_{d(off)}$			200		ns
Fall Time	t_f			65		ns
Diode Forward Voltage	V_{SD}	$I_S = 4.5\text{A}, V_{GS} = 0$			1.8	V

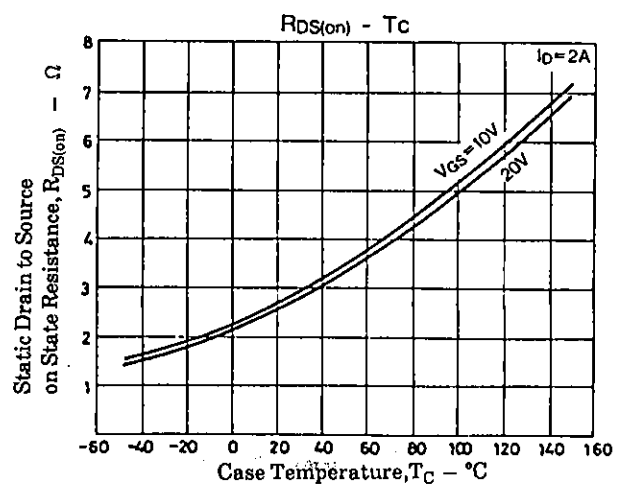
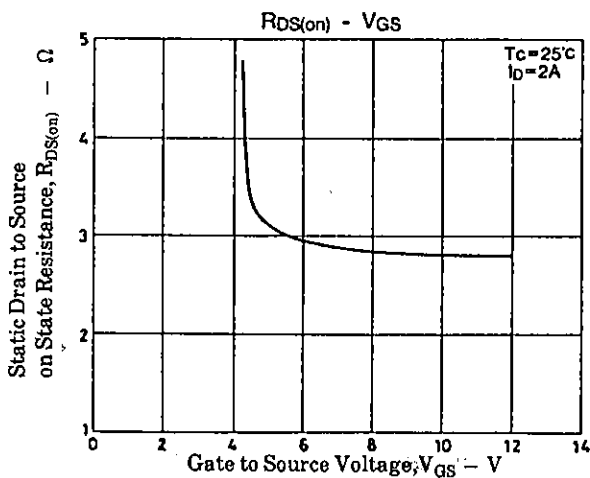
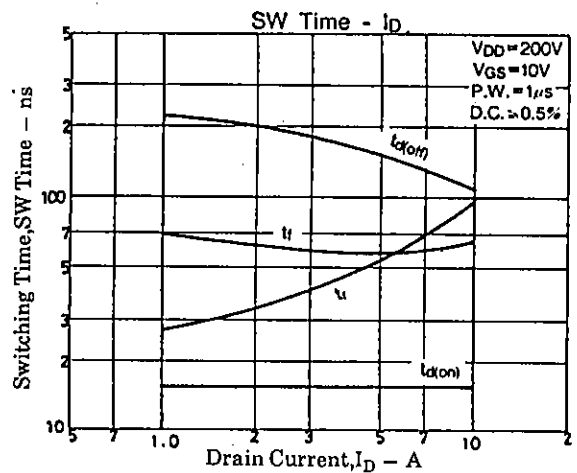
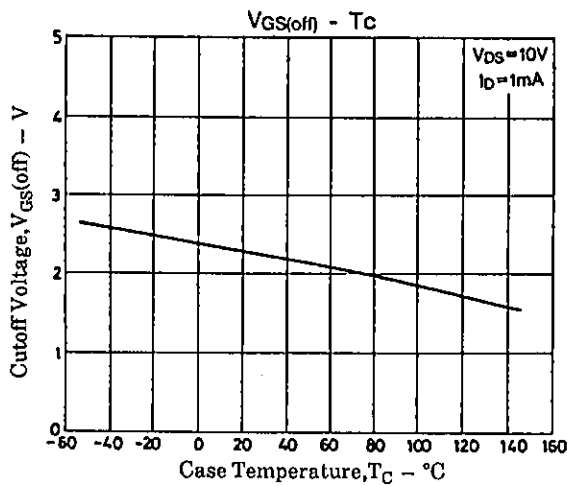
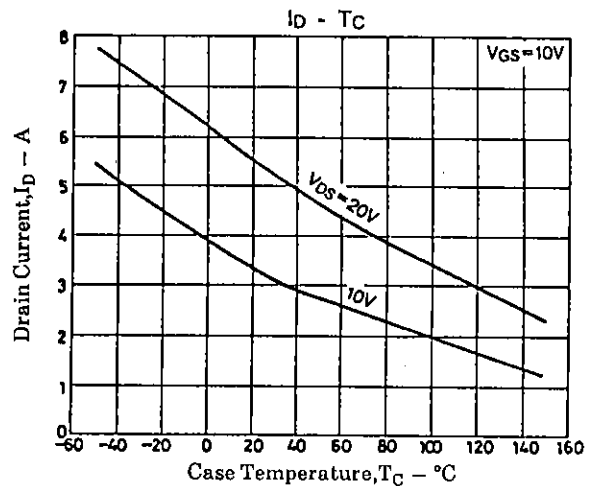
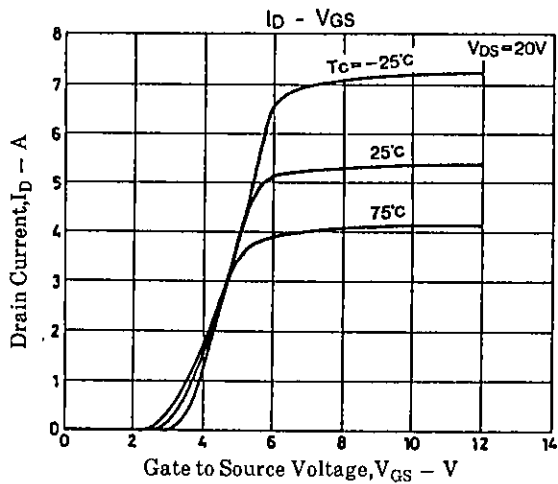
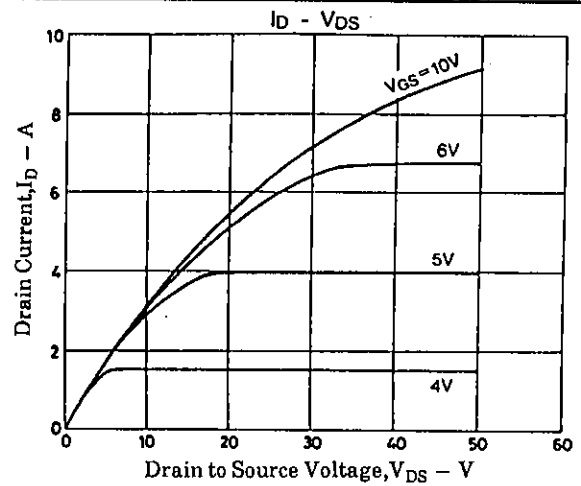
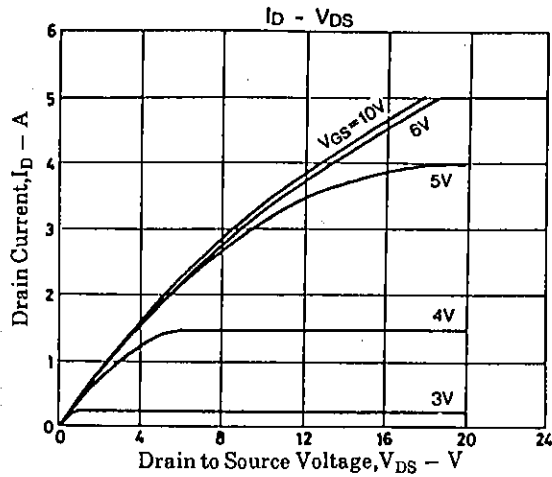
(Note) Be careful in handling the 2SK1463 because it has no protection diode between gate and source.

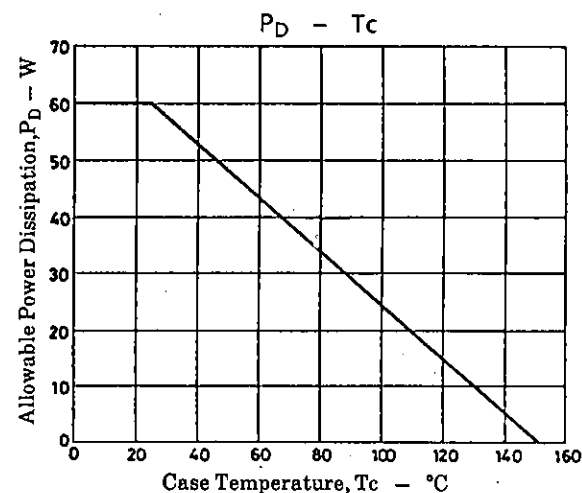
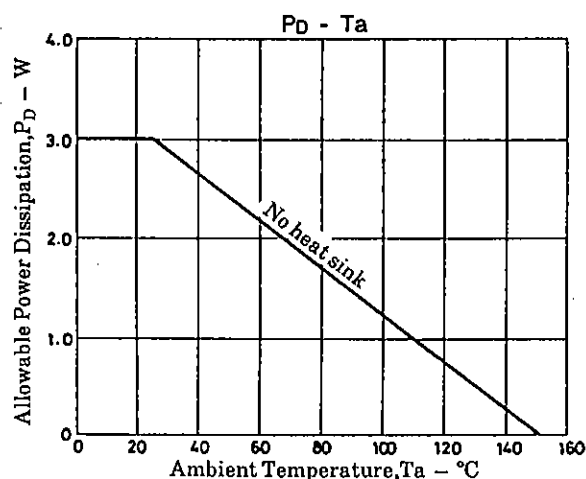
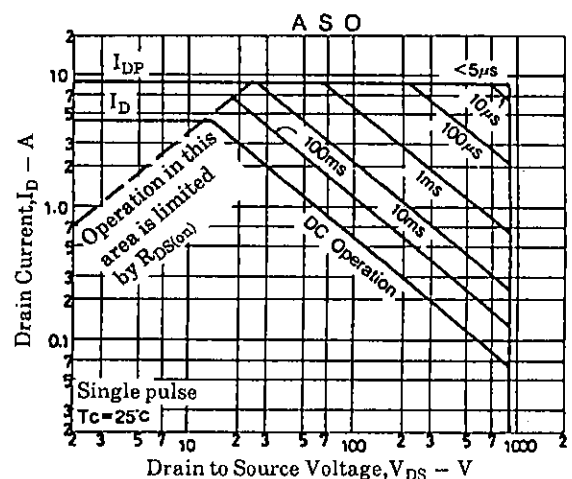
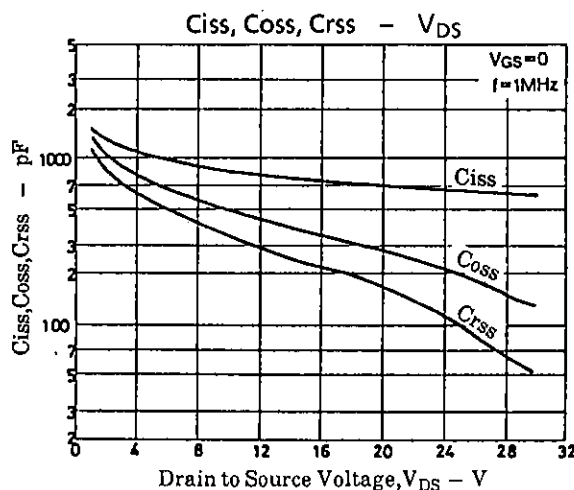
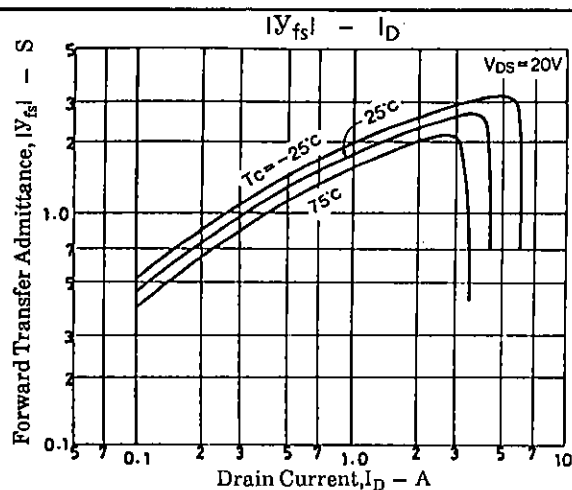
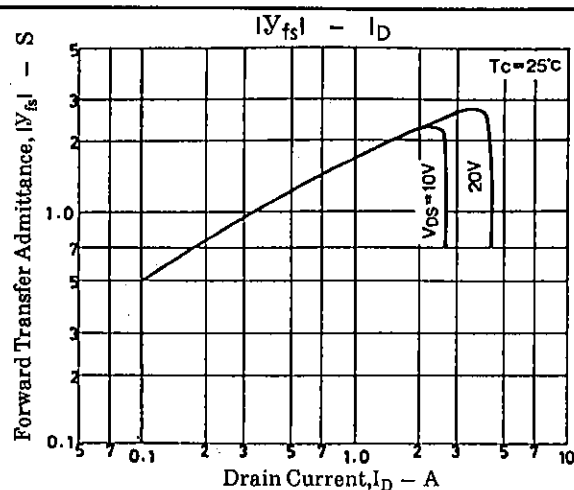
Switching Time Test Circuit**Package Dimensions 2076**

(unit: mm)



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